



# ACE2341B

## P-Channel Enhancement Mode Field Effect Transistor

### Description

The ACE2341B uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation gate voltages as low as 1.8V. This device is suitable for use as a load switch or other general applications.

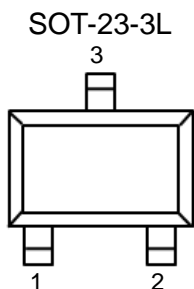
### Features

- $V_{DS}=-20V$ ,  $I_D=-4.1A$
- $R_{DS(ON)}<65m\Omega$  @  $V_{GS}=-4.5V$
- $R_{DS(ON)}<85m\Omega$  @  $V_{GS}=-2.5V$
- $R_{DS(ON)}<125m\Omega$  @  $V_{GS}=-1.8V$

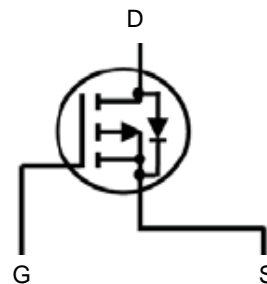
### Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current (Continuous)	$I_D$	$T_A=25^\circ C$	-4.1
		$T_A=70^\circ C$	-3.2
Drain Current (Pulse)	$I_{DM}$	-30	A
Power Dissipation	$P_D$	1.4	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

### Packaging Type

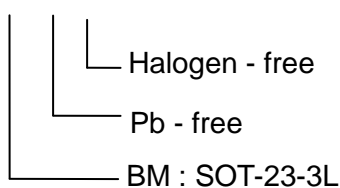


SOT-23-3L	Description
1	Gate
2	Source
3	Drain



### Ordering information

ACE2341B XX + H





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### Electrical Characteristics

$T_A=25\text{ }^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
State						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-16V, V_{GS}=0V$			-1	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$			$\pm 100$	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-4.3A$		55	65	m $\Omega$
		$V_{GS}=-2.5V, I_D=-2.5A$		70	85	
		$V_{GS}=-1.8V, I_D=-2A$		112	125	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.6	-0.81	-1.4	V
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-4A$		15		S
Drain Forward Voltage	$V_{SD}$	$I_S=-1.7A, V_{GS}=0V$		-0.85	-1	V
Switching						
Total Gate Charge	$Q_g$	$V_{DS}=-10V, I_D=-4.5A$ $V_{GS}=-4.5V$		8.92	11.6	nC
Gate-Source Charge	$Q_{gs}$			1.8	2.34	
Gate-Drain Charge	$Q_{gd}$			2.04	2.65	
Turn-On Delay Time	$T_{d(on)}$	$V_{DS}=-10V, R_L=10\Omega$ $I_D=-1A, R_{GEN}=6\Omega$ $V_{GS}=-4.5V$		16.08	32.16	ns
Turn-On Rise Time	$t_f$			5.28	10.56	
Turn-Off Delay Time	$t_{d(off)}$			37.6	75.2	
Turn-Off Fall Time	$t_f$			7.28	14.5	
Dynamic						
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V$ $f=1MHz$		800	960	pF
Output Capacitance	$C_{oss}$			131		
Reverse Transfer Capacitance	$C_{rss}$			103		

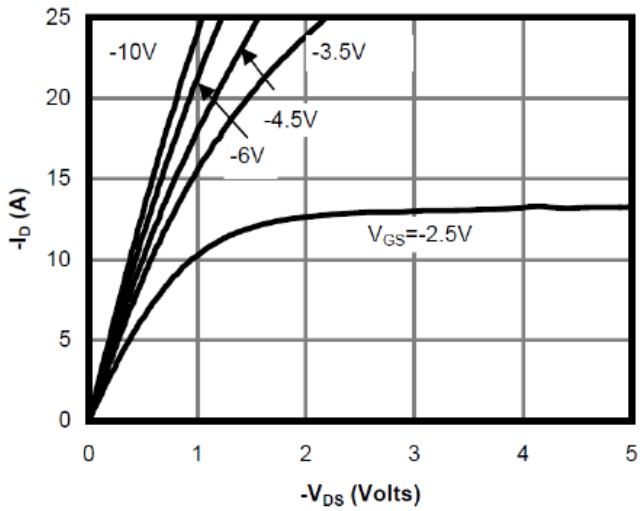
Note: 1. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25\text{ }^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

2. Repetitive rating, pulse width limited by junction temperature.

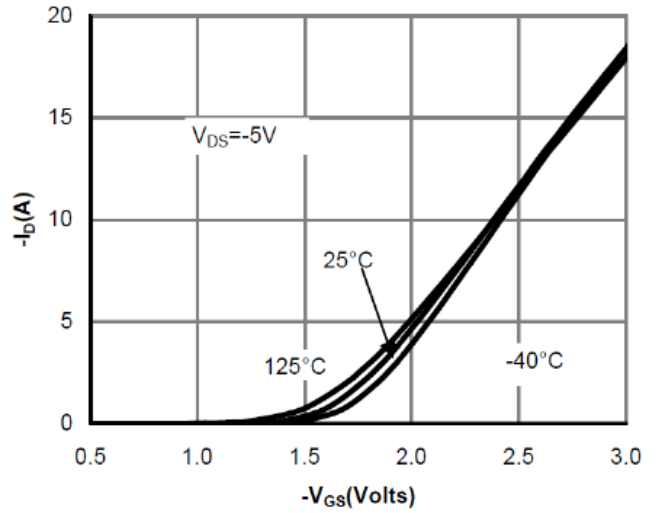
3. The current rating is based on the  $t \leq 10s$  junction to ambient thermal resistance rating.



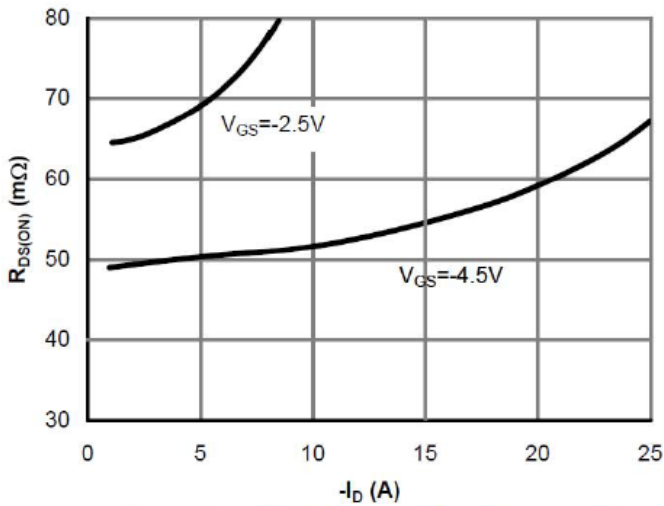
**Typical Performance Characteristics**



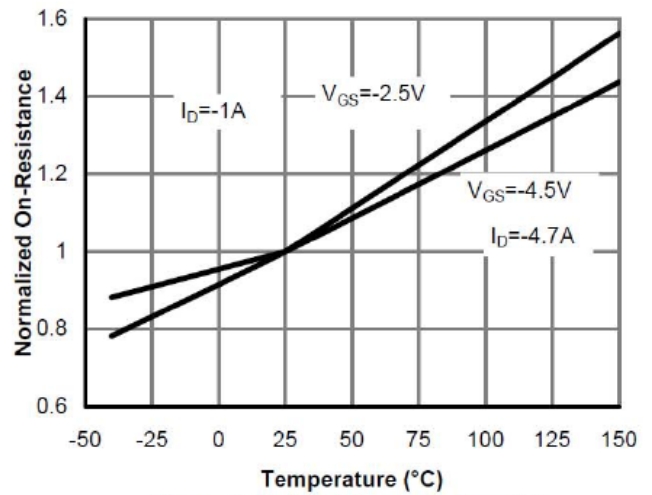
**Fig 1: On-Region Characteristics**



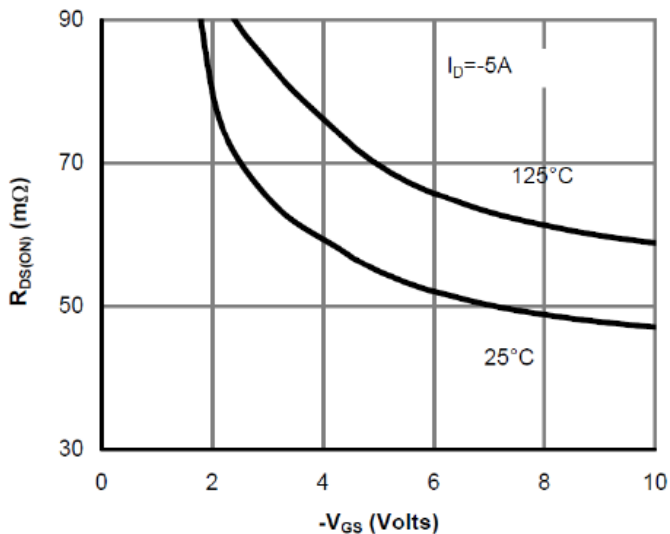
**Figure 2: Transfer Characteristics**



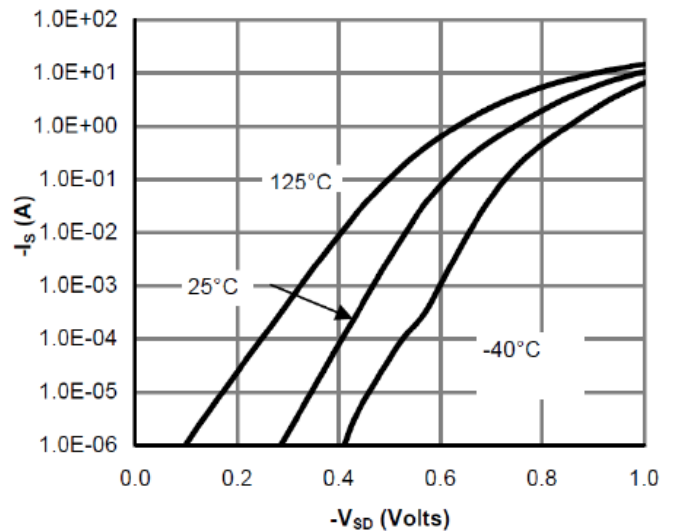
**Figure 3: On-Resistance vs. Drain Current and**



**Figure 4: On-Resistance vs. Junction**



**Figure 5: On-Resistance vs. Gate-Source Voltage**



**Figure 6: Body-Diode Characteristics**



### Typical Performance Characteristics

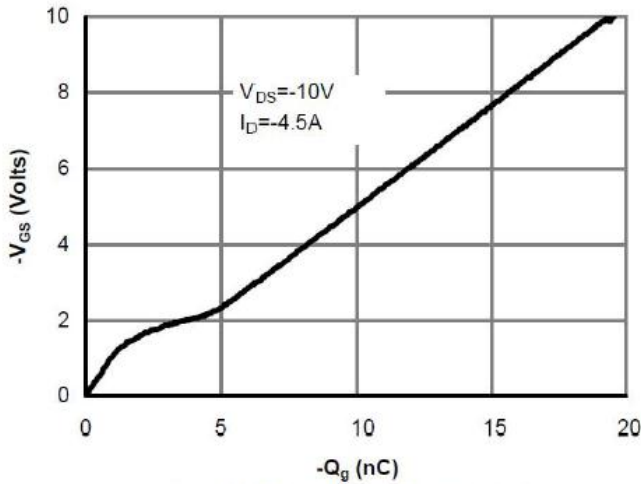


Figure 7: Gate-Charge Characteristics

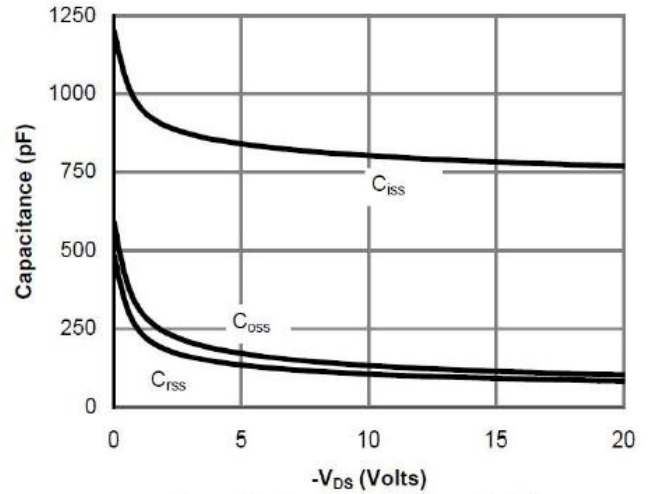


Figure 8: Capacitance Characteristics

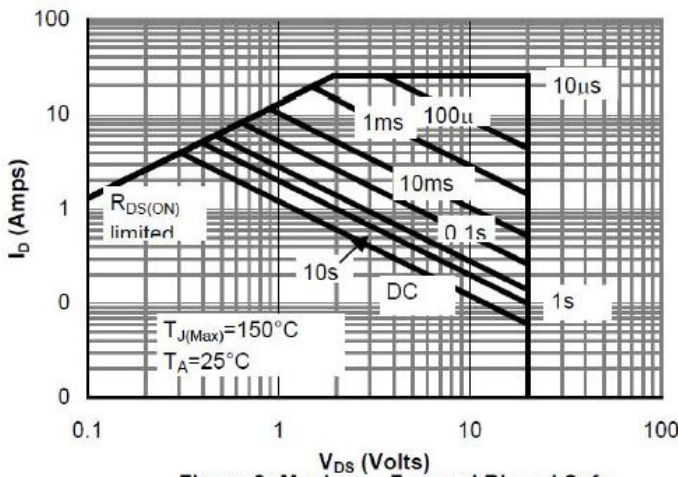


Figure 9: Maximum Forward Biased Safe Operating Area

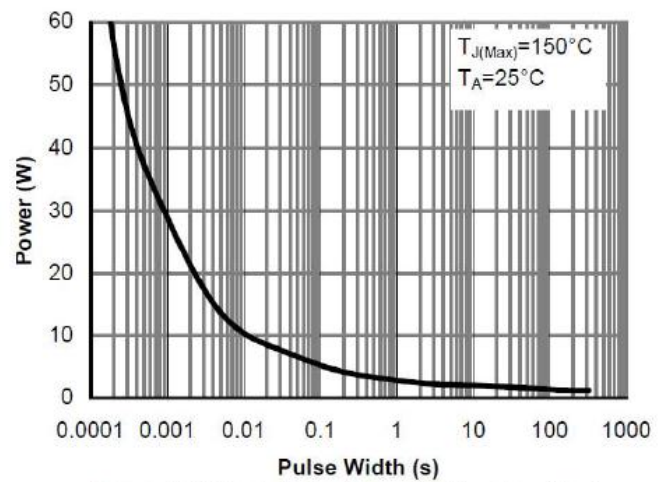


Figure 10: Single Pulse Power Rating Junction-to-Ambient

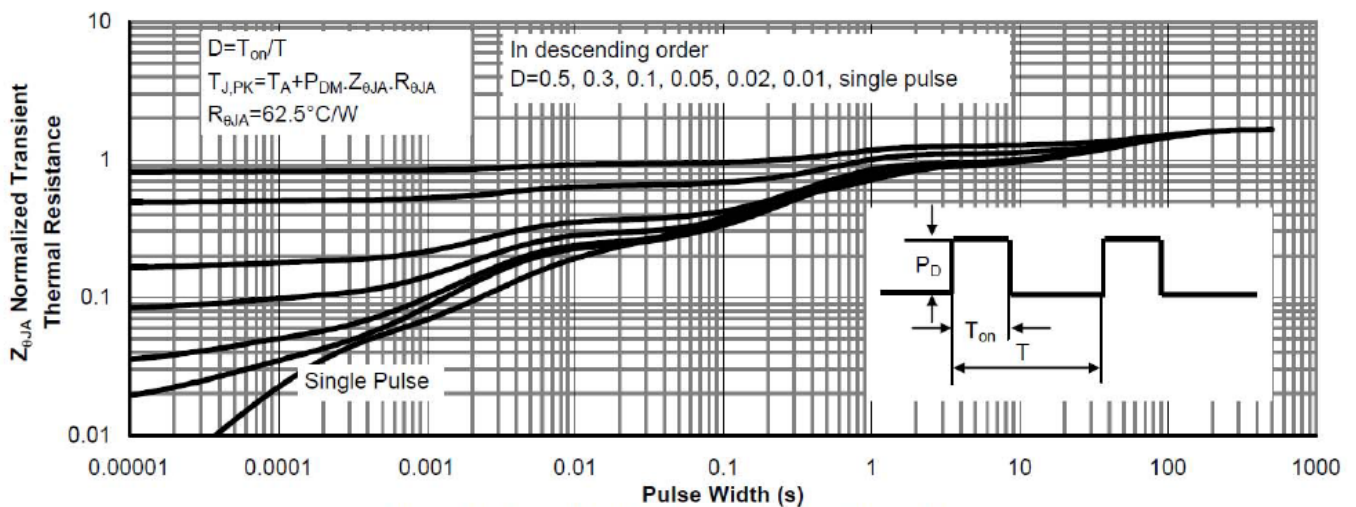


Figure 11: Normalized Maximum Transient Thermal Impedance

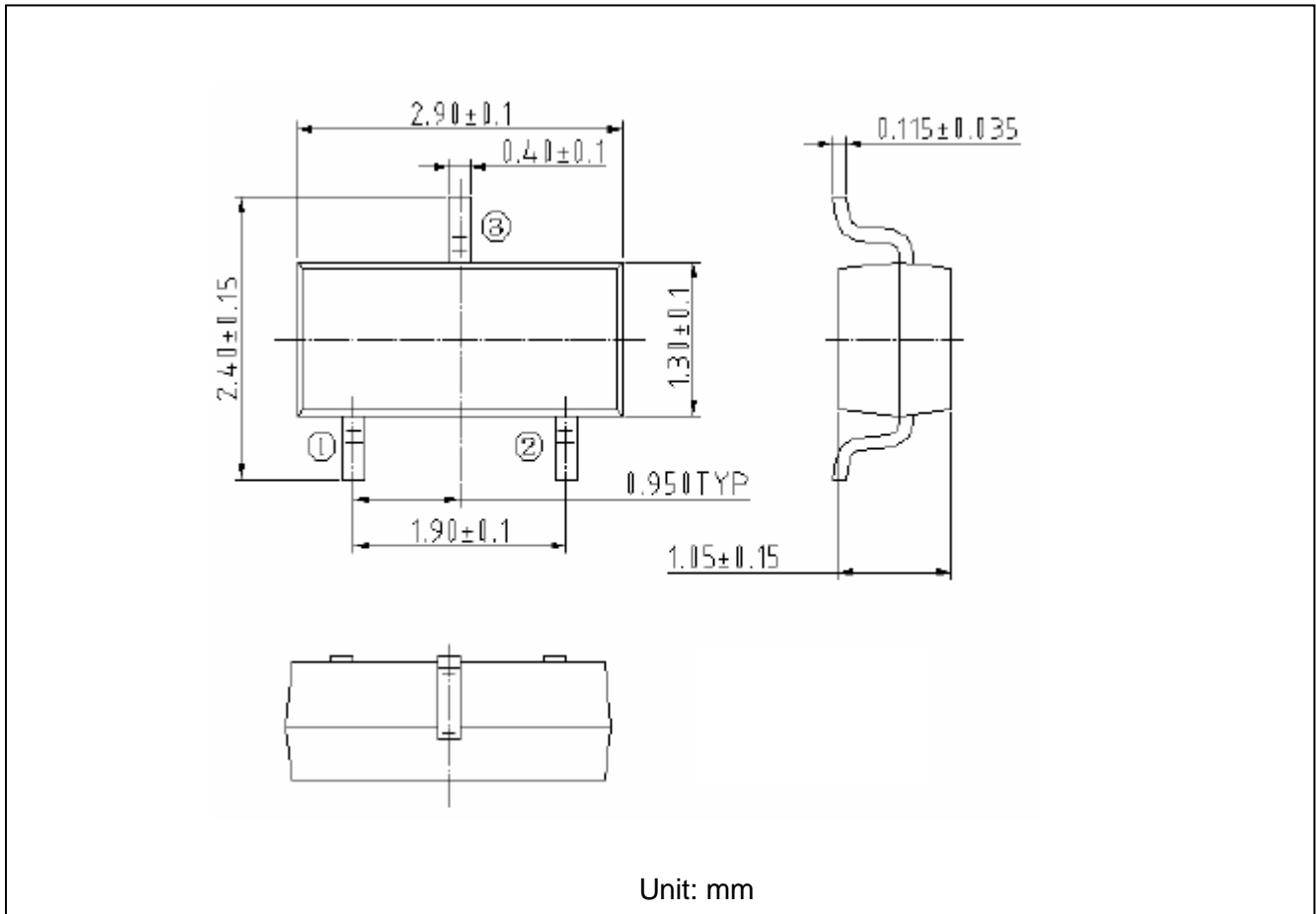


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### Packing Information

#### SOT-23-3L





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### Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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